

S1AF THRU S1MF General Purpose Rectifier Diodes

Features

- ●I_{F(AV)}
- •VRRM 50V-1000V
- High surge current capability

1A

Polarity: Color band denotes cathode

Applications

Rectifier

Marking

- S1X
 - X: From A To M

SMAF

Limiting Values(Absolute	Maximum Rating)
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		Unit		S1						
ltem	Symbol		Test Conditions	AF	BF	DF	GF	JF	KF	MF
Repetitive Peak Reverse Voltage	V _{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V _{RMS}	V		35	70	140	280	420	560	700
Average Forward Current	I _{F(AV)}	A	60Hz Half-sine wave , Resistance load , T_t=100 $^\circ$	1.0						
Surge(Non-repetitive)Forward Current	I _{FSM}	A	60Hz Half-sine wave, 1 cycle,Ta=25℃	30						
Operation Junction and Storage Temperature Range	T _J ,T _{STG}	°C		-55 ~ +150						

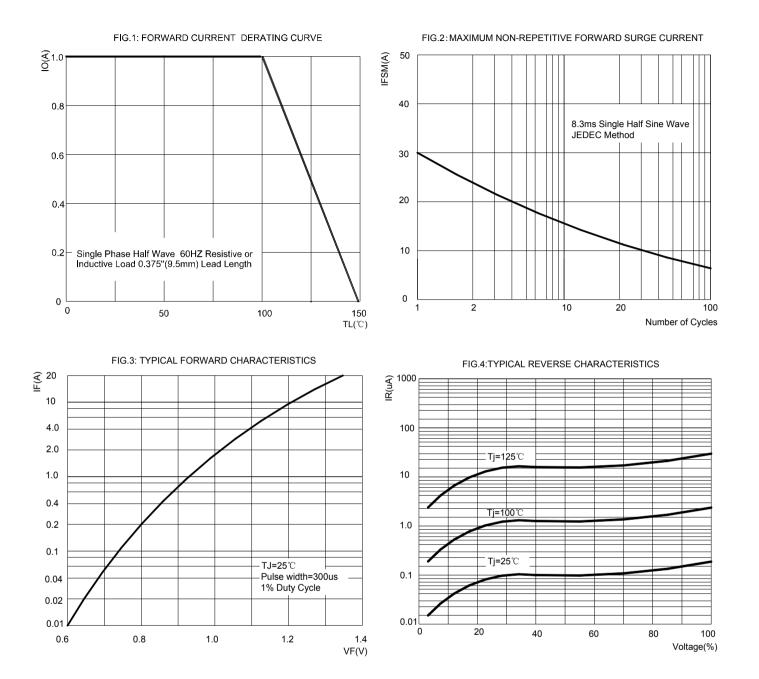
Electrical Characteristics (T=25°C Unless otherwise specified)

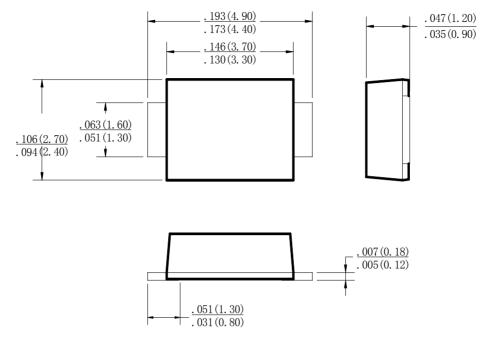
ltem	Symbol	Unit	Test Condition		МАХ
Peak Forward Voltage	V _F	V	I _F =1.0A		1.0
	I _{RRM1}	μA V _{RM} =V _{RRM}	T _a =25℃	5	
Peak Reverse Current	I _{RRM2}		V _{RM} =V _{RRM}	Ta=125℃	50
Thermal	$R_{_{ extsf{ heta}J}-A}$	°C/W	Between junction and ambient		55
Resistance(Typical)	R _{θJ-L}	C7 VV	Between junction and terminal		25

Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

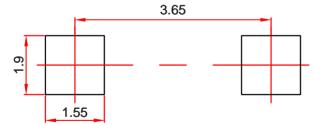
Typical Characteristics





Dimensions in inches and (millimeters)

SMAF Suggested Pad Layout



Note:

1.Controlling dimension:in millimeters.

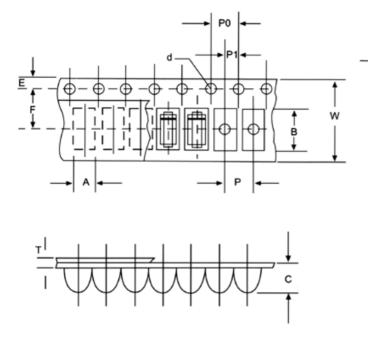
2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein.JSCJ does not assume any liability arising out of the application or use of any product described herein.

Reel Taping Specifications For Surface Mount Devices- SMAF



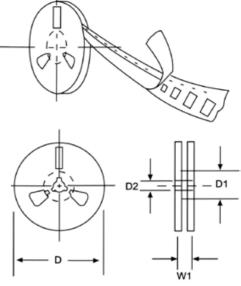


FIG: CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	A	2.83+0.1(0.112+0.004)
Carrier length	В	4.90+0.1(0.193+0.004)
Carrier depth	С	1.45+0.1(0.057+0.004)
Sprocket hole	d	1.55+0.05(0.061+0.002)
Reel outside diameter	D	178+2.0(7.0+0.079)
Reel inner diameter	D1	54±1.0(2.13±0.039)
Feed hole diameter	D2	13+0.5(0.512+0.020)
Strocket hole position	E	1.75+0.1(0.069+0.004)
Punch hole position	F	5.5+0.05(0.217+0.002)
Punch hole pitch	Р	4.0+0.1(0.157+0.004)
Sprocket hole pitch	P0	4.0+0.1(0.157+0.004)
Embossment center	P1	2.0+0.1(0.079+0.004)
Totall tape thickness	Т	0.23-0.29(0.009-0.011)
Tape width	W	12.0+0.1(0.472+0.004)
Reel width	W1	16.8+2.0(0.661+0.079)

NOTE: Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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